

IMPROVED PROCESS FOR DEPOSITION OF SEMICONDUCTOR FILMS

Abstract of the Disclosure

Chemical vapor deposition processes utilize higher order silanes and germanium precursors as chemical precursors. The processes have high deposition rates yet produce more uniform films, both compositionally and in thickness, than films prepared using conventional chemical precursors. In preferred embodiments, trisilane is employed to deposit SiGe-containing films that are useful in the semiconductor industry in various applications such as transistor gate electrodes.

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